User's Manual

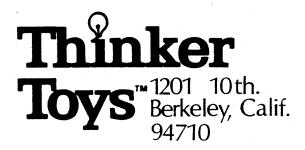
Econoram |||*

SYNCHROFRESH VIIITM

S-100 Buss Compatible

8K Random Access Memory

Introduction	1
Operating Instructions	2
Theory of Operations	5
Memory Diagnostic	9
Parts List	14
Assembly Instructions	16
Power-Up and System Check-Out	20
Warranty	22
Compatibility	· 23
Schematic Drawings	24



Synchrofresh TM VIII Memory Systems

INTRODUCTION

Dynamic memory has two very attractive features: It is less expensive to manufacture than static and it consumes significantly less power. Both of these attributes stem from the extremely simple cell design of a dynamic device. Typical static memory cells require four transistors as opposed to one for the dynamic part. This simplicity of design results in much smaller devices. And, small devices require less power. They also result in higher yields which mean a lower cost per bit.

There are, however, certain penalities which accrue from low cost and low power consumption: dynamic memorys require periodic refreshing. Thus a memory product which uses dynamic devices must include extra control logic to produce the required refresh cycles. This usually results in complicated designs with more parts and, therefore, more power and reduced reliability.

Until now, most of the memory designers in the small computer market have stayed with static devices for design simplicity. Those who attempted to use dynamic parts have been plagued with troublesome units (most notable MITS of Altair fame) or have had extremely complicated circuit boards. One unit has over thirty-five control circuits plus a delay line, and another is made with a five layer board to accomodate all the needed signal traces.

What has been missing from past designs is a scheme to make the refresh control logic both simple and reliable. Synchrofresh is just that. Synchrofresh stands for synchronized refresh -- a refresh scheme which derives its timing directly from the S-100 buss just as static memory boards do. This eliminates the possibility of a conflict. Both memory access and refresh timing are woven into the same clock signals which eminate from the CPU. The natural timing from the buss insures a reliable memory refresh. But these same buss signals also simplify the control logic necessary to perform this refresh. The result is a memory which behaves just as if it were static but with two big differences: the cost is lower (\$100 cheaper than some 8K static boards) and the power consumption is drastically cut (typically by a third).

^{*}Econoram is a trademark of Godbout Electronics

OPERATION

GENERAL

The Synchrofresh 8K memory unit is an S-100 compatible product. It contains two completely independent 4K blocks. Each of these two 4K blocks may be placed on any 4K address boundary -- the addressing details are presented below.

The physical design allows stacking on 3/4" centers (this is the spacing used in most of the S-100 buss boards such as the 20-slot WunderBuss). A hardwired write enable switch is included on the board to provide a foolproof method of protecting data stored in the memory.

In the paragraphs which follow, reference will be made to positions of different parts on the circuit board. In all cases, the orientation of the circuit board is that the gold fingered edge connector is at the bottom of the board. This places the voltage regulators on the left side of the board while the memory array is toward the right and to the top.

MAINTENANCE

Assembled Synchrofresh memories carry a one year warranty against defects. The only required maintenance is to run the memory test included with this manual or a reasonable substitute if you suspect that the unit is not functioning properly. If the memory should fail to operate properly and has not been damaged or subjected to abuse (as determined by us), it will be repaired or replaced at no charge during the warranty period.

WRITE PROTECTION

At the top of the circuit board just above position 2A, there is a three-position slide switch. The left and middle positions are both write enable states while the right position is the write protect state.

When the board is to be used as read/write memory, the slide switch should be to the left or in the center. In these positions, the CPU can write into or read from either 4K memory block.

When the unit is to be used as "read only" memory, the slide switch should be in the right most position. In this position, write commands issued to the memory by the CPU or DMA devices are ignored.

The write protect mode is especially useful when it is necessary to prevent a program or data from being accidently destroyed by another program or from the front panel.

ADDRESSING

The 8,192 byte memory array on the Synchrofresh board is divided into two 4,096 byte sections. The addressing of these two sections is controlled by an eight position dip switch located at position 1F toward the bottom and to the left of the board.

The left four switches (1 through 4) are dedicated to one 4K block while the right four switches (5 through 8) control the other 4K block.

Block \emptyset occupies positions 4C (bit \emptyset), 5C (bit 1), 6C (bit 2), 7C (bit 3), 4B (bit 4), 5B (bit 5), 6B (bit 6), and 7B (bit 7).

Block 1 occupies positions 4D (bit \emptyset), 5D (bit 1), 6D (bit 2), 7D (bit 3), 4A (bit 4), 5A (bit 6), 6A (bit 6), and 7A (bit 7).

4K address boundaries have a hexidecimal expression of the form X000 where X is some hexidecimal digit between Ø and F. Thus, one four bit hexidecimal digit is sufficient to determine the addressing of a 4K block of memory which resides between 4K address boundaries. Since each switch position corresponds to a bit position within a hex digit, you can see how an eight position dip switch can control the addressing of two 4K blocks of memory.

The relative positions of the switches correspond to the relative bit positions within a hex digit. That is, the left most switch of each group of four (switch #1 or #5) has the highest numeric weight while the right most switch of each group (switch #4 or #8) has the lowest numerical weight. A switch in the "on" position or to the top signifies a zero bit while a one bit is obtained by pulling the switch down.

Consider a practical example in the use of the address selecting dip switch. The two 4K blocks are designated block \emptyset and block 1. The left four switches control block \emptyset and the right four switches control block 1. Suppose block \emptyset is to be located at $(A\emptyset\emptyset\emptyset)_{16}$ and block 1 at $(7\emptyset\emptyset\emptyset)_{16}$. The left four switches must then express 1010 which is the binary for the hex digit A while the right four switches must show 0111 which the binary equivalent of 7. Since an "on" or "up" position corresponds to a \emptyset while an "off" or "down" position corresponds to a 1, the switches should be arranged as follows:

SW 1	SW 2	SW 3	SW 4	SW 5	SW 6	SW 7	SW 8
off	on	off	on	on	off	off	off
down	uр	down	up	up	down	down	down
	O	1		0	1 7	1	1

Below is a table of possible starting addresses along with switch pattern corresponding to these addresses.

Switch No.

Block /	Α		1	2	3	4
Block E	3		5	6	7	8
Startin	ng Address:		·			
<u>Hex</u>	<u>Octal</u>					
0000	000:000		on	on	on	on
1000	020:000		on	on	on	off
2000	040:000		on	on	off	on
3000	060:000	·	on	on	off	off
4000	100:000		on	off	on	on
5000	120:000		on	off	on	off
6000	140:000		on	off	off	on
7000	160:000		on	off	off	off
8000	200:000		off	on	on	on
9000	220:000		off	on	on	off
A000	240:000		off	on	off	on
B000	260:000	·	off	on	off	off
C000	300:000		off	off	on	on
D000	320:000		off	off	on	off
E000	340:000		off	off	off	on
F000	360:000		off	off	off	off

THEORY OF OPERATION

GENERAL

Synchrofresh was designed with two primary objectives -- that it be reliable and foolproof. Ideally, dynamic memory should be reliable, low in cost, and with power consumption well below comparable static memory units. The user should be able to purchase dynamic memory with the same confidence he has shown in the static.

The objectives of low cost and low power consumption have been met in Synchrofresh. Although extensive tests have been performed, true reliability cannot be measured until the memories have been used in varying applications in the field over a length of time. Unquestionably, the design innovation of this memory is a break through. It dispenses with the usual complicated timing mechanisms — the one shots and crystal oscillator have been eliminated and replaced with simple timing derived from the ϕ_2 and PSYNC signals on the S-100 buss.

DATA BUFFERS

A peculiarity of the 2107B type part is that the input and output data have the opposite polarity. The input data to the array from the S-100 buss is buffered by two 74LSØ4/14 inverters at positions 3B and 3C to accommodate the polarity problem. The output data from the memory array to the S-100 buss is latched and buffered by a 74LS373/S373. This is one of the newer twenty-pin octal parts being introduced by Texas Instruments and other vendors. This part is both a transparent latch and a tri-state* buffer. Moreover, it is a full eight bits wide making it a very desirable part for microprocessor applications.

The input buffers are active at all times while the output buffer is active only when the board has been selected and the data input strobe PDBIN is active.

ADDRESS BUFFERS/MULTIPLEXORS

Addresses to the memory from the S-100 buss and the refresh address counter are buffered and selected through three 74LS157/158/257/258 quad two-input multiplexors. The control input to the multiplexors comes from a D- flip-flop at 3A which switches data and refresh addresses to the array at the proper times. A careful examination of the timing of this flip-flop will reveal that addresses are switched in the middle of a memory cycle. This would be unacceptable were we using static RAMs. The situation with dynamic RAMs is somewhat different. The address inputs of a dynamic RAM chip are not only buffered but also latched. This latching occurs with the rising edge of CENBL, the signal which initiates a cycle for the memory chip. The main concern with the address signals to the 2107B is that they are stable at the rising edge of CENBL and remain so for approximately 150 ns. In the present case, the MUX CNTL signal does

^{*}Trade mark of National Semiconductor.

not change for 250 ns after the rising edge of CENBL, giving a margin of 100 ns.

REFRESH ADDRESS COUNTER

The refresh address for the array are generated by the 74393 at 3E which is a dual hex counter. This counter advances at the falling edge of its clock inputs (pins 1 and 13). The signal REFRESH drives the primary clock input at pin 1. This signal is high during memory refresh cycles. Thus, the refresh addresses change upon termination of a refresh cycle and are stable throughout memory refreshes. This is a desirable state of affairs in view of the preceeding discussion concerning address signal stability requirements for the 2107B.

ADDRESS SELECTION LOGIC

Block starting addresses are determined using four of the DIP switches and a 74LS266. This device is a quad 2 input comparator with open collector outputs. This is an example of an extremely efficient use of open collector logic. The standard methods for selecting addresses are with a 4 or 6 bit comparator or using a pair of 1 of 4 decoders in series. The former uses parts costing from four to eight times that of the 74LS266 and the latter uses twice as many switches and a part which costs twice as much as the 74LS266.

During the late sixties and early seventies, logic designers used far too much open collector logic. The cause of this was their inability to avoid habits acquired when designing with DTL (diode-transistor logic). One of the characteristics of DTL is that all the outputs have either an open collector or a collector with an internal pull-up resistor. Either structure facilitates the use of so called "wired OR" logic. This is exactly the way the outputs of the 74LS266 are connected (see page 1 of the schmatics). The only way the connected outputs can be high is when each pair of inputs is individually at the same logic state, ie, the switch positions correspond one for one with the address A15, A14, A13, and A12.

The major disadvantage of open collector logic is that the transition time from the logic zero state to the logic one state is slow (the resistor has to do the work charging a collector which looks like a capacitor when the device is off). In our case, the slow rise times are of no consequence since the 8080A puts its addresses on the buss very early. TTL and more recently tri-state LS TTL have replaced most of the old DTL open collector designs. However, keep in mind that though the active outputs of TTL are usually superior, the older open collector structures still have their uses.

BOARD SELECTION LOGIC

The 74LSØ2 at position 3D performs most of the board selection logic using the outputs of the two 74LS266 along with the buss signals SINTA, SINP, and SOUT. If SOUT is zero and SINP is zero and SINTA is zero and ENBL A or ENBL B is true, the board is selected at the rising edge of ϕ_2 when PSYNC is active. As a practical matter, this is the earliest time when all the status signals and address signals are stable. The rising edge of ϕ_2 during the active state of PSYNC also starts a memory access cycle assuming that the board selection logic permits it.

CHIP ENABLE CIRCUITRY

The chip enable input pin of the 2107B memory chip is the only pin that is not TTL compatible. This input must swing between zero and twelve volts. Moreover, these swings in voltage cannot take more than 40 ns. This is the signal which initiates a memory cycle for the 2107B and the rising edge of this signal activates the data buffers, the many internal sense amplifiers and the address buffers and latches. This activation period is the major source of noise on the various voltage lines since so much circuitry within the memory chips abruptly begins to use power and current. The large number of ceramic and tantalum capacitors in and around the memory array is used to absorb this noise and insure adequate signal-to-noise ratios. Transistors Q_1 and Q_2 are driven with a classical "boot strap" circuit. While the transistors are off, capacitors C75 and C76 are charged through the diode resistor pairs CR3, R4 and CR5, R6 to approximately 11 volts.

When the 7406s turn off, C75 begins discharging through R4 and R5 and the base of Q1. But the emitter of Q1 cannot be more than .7 volts less than the base. Thus, the emitter begins to rise. But, as the emitter rises, so does the emitter side of C75. And, since the voltage across C75 cannot change instantaneously, the R4 side of C75 is forced to rise above 11 volts. In fact, for a short period of time, the voltage difference across C75 will remain approximately 11 volts. The fact that the voltage across a capacitor cannot change instantaneously causes the emitters of Q1 and Q2 to snap up to within 11.6 volts very rapidly. Typically, in 25 ns. When the 7406s turn on again, the bases of Q1 and Q2 are pulled down by one pair of 7406s to turn the transistors off while the other pair of 7406s insure that the emitters are pulled below .4 volts.

This circuit is very fast with almost no over shoot at either 12 volts or ground.

TIMING AND CONTROL LOGIC

The heart of the timing and control circuitry is the 74LS161 hex counter. This counter goes through two types of cycles depending on the length of the buss memory cycle and implements a so called "finite state" machine. During buss memory cycles consisting of T_1 , T_2 , and T_3 states, the counter counts from zero to two synchronous with PSYNC. During buss memory cycles which have four or more T states between one PSYNC and another, the counter counts from zero to three and back to zero again. This counter directs all the other control circuitry on the board. Each state of the counter consists of two phases: when ϕ_2 is a logic zero (which we label phase A) and when ϕ_2 is a logic one (which we call phase B). The counter advances on the falling edge of ϕ_2 . To better understand the control circuitry, we shall discuss what happens with the memory at each phase of each state of the counter. For simplicity, we will assume that the zero state is simultaneous with PSYNC.

- Zero Phase A
 Memory chip precharge time (CE low). The address multiplexors
 are switched to the S-100 address buss lines and away from the
 refresh counter addresses. Chip select lines conditionally
 enabled.
- Zero Phase B Memory cycle is started and data latch is enabled.
- One Phase A Memory cycle continues; latch is still enabled.
- 4. One Phase B
 Address multiplexors are switched from S-100 address buss to refresh counter outputs and chip select lines disabled.
- 5. Two Phase A

 Memory cycle terminated; data latch disabled.
- Two Phase B Memory chip precharge time (CE low).
- 7. Three Phase A Refresh cycle started.
- 8. Three Phase B
 Refresh cycle continues.

MEMORY DIAGNOSTIC

The memory test described below was designed by Phil Meads of William Brobeck Associates to exercise the most sensitive circuitry of 22 pin NMOS 4k dynamic memory chips: the address buffers and latches. The test starts from the middle and works its way outward alternately to the top and bottom of memory. This type of test inverts the address lines more often than sequential ones. This continual inversion process punishes and eventually breaks down weak or faulty address buffers in the device.

USING THE TEST

The test itself <u>must</u> be placed in an area which is different than the location of the board(s) to be tested. The test starts on a page boundary to make the task of relocating the binary code easier.

There are <u>two</u> parameters in the test to be set by the user:

- (1) The number of 4k blocks to be tested -- keep in mind that there are two 4k blocks per board. This constant is called BLKCNT and is located at the eleventh byte of the test.
- (2) The starting page number of the <u>lowest</u> 4k block to be tested is called PAGENO and is located at the ninth byte of the test.

When testing more than one 4k block of memory, be sure that they occupy contiguous memory.

The page number of the position of the test itself must be entered wherever a (YYY)8 or (YY)16 occurs in the test listing. This is necessary because JMP and CALL need both the page number and the location within the page to execute correctly.

The only other thing to remember when loading the test is that it must be placed at the starting address of a page.

Start the test at the first instruction. Once started, the test will run continuously unless an error is detected. If the test encounters an error, all the data pertinent to this error is stored in the last ten locations of the test. After storing this data, the test comes to a dynamic halt at the label STALL. The test may be restarted by stopping the computer and restarting it at the POP PSW instruction following JMP STALL. The user may also restart the test from the beginning. If errors indicate the board is malfunctioning, return it as soon as possible for warranty service.

For \$4.95 a cassette tape of both the source and binary of the memory test recorded in the Kansas City Standard 300 baud format is available. It auto loads into the RAM of the Speakeasy I/O board which is also available from Thinker Toys.

MEMORY TEST PROGRAM FOR 4K NMOS RAMS (Octal)

YYY 000 061 175 YYY 003 001 000 000 006 305 007 006 100 011 016 002 013 041 377 007 016 170 017 204 020 147 021 345 022 315 114 YYY 025 167 026 315 123 YYY	NEWCYL LOOP WRITE	MV I MV I LX I MOV ADD MOV PUSH	B,Ó B B,PAGENO	INITIALIZE CYCLE COUNT UPDATE CYCLE COUNT STARTING ADDR OF TEST MEM NO. OF 4K BLOCKS TO TEST HALF SIZE OF MEMORY -1 CALCULATE MIDDLE OF CURRENT BLOCK SAVE INITIAL ADDRESS GET TEST WORD STORE
031 315 114 YYY 034 167 035 315 134 YYY 040 302 022 YYY 043 341		CALL MOV CALL JNZ POP	TWORD M,A INCR WRITE H	STORE
YYY 044 315 114 YYY 047 256		CALL XRA CNZ CALL XRA CNZ CALL XRA CNZ CALL JNZ MVI ADD MOV DCR JNZ MOV ADI MOV POP INX JMP		GET TEST WORD COMPARE COMPLEMENT ADDRESS GET TEST WORD COMPARE COMPLEMENT AND DEC ADDRESS ADVANCE THE BLOCK DECREMENT BLOCK COUNT CALCULATE NEW BASE FOR TEST WORD
114 175 115 007 116 207 117 204 120 203 121 127 122 311	TWORD	MOV RLC ADD ADD ADD MOV RET	A,L A H E D,A	GET LOWER BYTE OF ADDRESS ROTATE SHIFT ADD HIGHER BYTE OF ADDR ADD BASE SAVE TEST WORD

YYY 123 174 124 356 017 126 147 127 175 130 356 377 132 157 133 311	COMP MOV XRI MOV MOV XRI MOV RET	A,H 17Q H,A A,L 377Q L,A	COMPLIMENT THE UPPER BYTE ADDRESS WITH RESPECT TO MEM SIZE COMPLIMENT THE LOWER BYTE OF THE ADDRESS
YYY 134 315 123 YYY 137 053 140 300 141 170 142 075 143 274 144 311	INCR CALI DCX RNZ MOV DCR CMP RET	COMP H A,B A	RESTORE ADDRESS TO NORMAL STATE DECREMENT TEST IF LOWER BYTE ZERO TEST UPPER BYTE EQUAL TO BLOCK BOUNDARY
YYY 145 345 146 305 147 325 150 365 151 303 151 YYY 154 361 155 321 156 301 157 341 160 311	ERROR PUSI PUSI PUSI PUSI STALL JMP POP POP POP RET	H B H D H PSW STALL PSW D	SAVE ERROR ADDRESS SAVE CURRENT BLOCK SAVE TEST WORD SAVE ERROR BITS DYNAMIC HALT RESTORE THE STATE OF THE CPU
YYY 161 000 162 000 163 000 164 000 165 000 166 000 167 000 000 171 000 000 173 000 000	TABLE DB DB DB DB DB DB DB DW DW DW STACK DW	0 0 0 0 0 0 0	FLAGS ACC - 1S ARE ERROR BITS E - CURRENT RANDOM OFFSET D - CURRENT TEST WORD C - CURRENT BLOCK COUNT B - CURRENT BLOCK PAGE HL - ERROR ADDRESS RETURN ADDRESS CYCLE COUNT

MEMORY TEST PROGRAM FOR 4K NMOS RAMS (Hex)

YY 00 03 06 07 09 0B 0E 0F 10	C5 06 40 0E 02 21 FF 07 78 84 67	START NEWCYL LOOP	LXI PUSH MVI MVI LXI MOV ADD MOV	SP,STACK B,O B B,PAGENO C,BLKCNT H,7:377Q A,B H H,A
11 12 15 16 19 10 1D 20 23	E5 CD 4C YY 77 CD 53 YY CD 4C YY 77 CD 5C YY C2 12 YY E1	WRITE	PUSH CALL MOV CALL CALL MOV CALL JNZ POP	H TWORD M,A COMP TWORD M,A INCR WRITE H
YY 24 27 28 2B 2E 31 32 35 38	CD 4C YY AE C4 65 YY CD 53 YY CD 4C YY AE C4 65 YY CD 5C YY C2 24 YY	READ	CALL XRA CNZ CALL CALL XRA CNZ CALL JNZ	TWORD M ERROR COMP TWORD M ERROR INCR READ
YY 3B 3D 3E 3F 40 43 44 46 47 48 49	3E 10 80 47 0D C2 0B YY 7B C6 87 5F C1 03 C3 06 YY		MVI ADD MOV DCR JNZ MOV ADI MOV POP INX JMP	A,20Q B B,A C LOOP A,E 135 E,A B
YY 4C 4D 4E 4F 50 51 52	7D 07 87 84 83 57	TWORD	MOV RLC ADD ADD ADD MOV RET	A,L A H E D,A

YY 53 54 56 57 58 5A 5B	7C EE OF 67 7D EE FF 6F C9	COMP	MOV XRI MOV MOV XRI MOV RET	A,H 17Q H,A A,L 377Q L,A	
YY 5C 5F 60 61 62 63 64	CD 53 YY 2B CO 78 3D BC C9	INCR	CALL DCX RNZ MOV DCR CMP RET	COMP H A,B, A	
YY 65 66 67 68 69 6C 6D 6E 6F 70	E5 C5 D5 F5 C3 69 YY F1 D1 C1 E1	STALL	PUSH PUSH PUSH JMP POP POP POP POP RET	H B D PSW STALL PSW D B H	
YY 71 72 73 74 75 76 77 79 78 7D	00 00 00 00 00 00 00 00 00 00 00 00	TABLE	DB DB DB DB DB DB DB DW DW DW DW	0 0 0 0 0 0 0	FLAGS ACC - 1S ARE ERROR BITS E - CURRENT RANDOM OFFSET D - CURRENT TEST WORD C - BLOCKS LEFT TO TEST B - CURRENT BLOCK PAGE HL - ERROR ADDRESS RETURN ADDRESS CYCLE COUNT

KIT PARTS LIST

	1	8" x 10" glossy photograph of assembled board
-	1	5" x 10" circuit board with solder mask
	2	.027 µfd capacitors
	46	.011 μfd disk capacitors*
•	24	2.7 µfd tantalum capacitors
-	14	39 µfd tantalum capacitors
	2	2N3904 transistors
45 Maria	4	1N914/4820-0201 signal diodes
	1	1N751/1N5231 5-volt zener diode
	1	7805/LM340-5 +5-volt regulator
	1	78M12/7812/LM340-12 +12-volt regulator
	14	14-pin low profile sockets
-	4	16-pin low profile sockets
	1	20-pin low profile socket
() 	16	22-pin low profile sockets
	1	double-pole single throw PC mount slide switch
	1	8 position DIP switch
-	1	750Ω $\frac{1}{2}$ watt resistor purple-green-brown
	2	200Ω $\frac{1}{4}$ watt resistors red-black-brown
	4	510Ω ¼ watt resistors green-brown-brown
	2	910Ω ¼ watt resistors white-brown-brown
	9	$3.3k\Omega$ $\frac{1}{4}$ watt resistors orange-orange-red
-	1	74LS00 quad 2 input NAND gate
	1	74LS02 quad 2 input NOR gate

^{*}by-pass capacitors - value will vary from .01 μ fd to .1 μ fd depending on current supply.

 1	7406 hex inverter/buffer
 2	74LS08 quad 2 input AND gate
 1	74LS10 triple 3 input NAND gate
 3	74LS14/74LS04 hex inverter/Schmidt trigger
 2	74LS74 dual D- flip-flop
3	74LS158/74LS258 quad 2 input inverting multiplexor
 1 -	74LS160/74LS161/74LS162/74LS163 hex/decade counter
 2	74LS266 quad 2 input EXCLUSIVE NOR gates
 1	74LS373/74S373 octal latch/tri-state* buffer
1	74LS393/74393 dual hex counter
16	2107B/RM1701/MM5280 4096 x 1 dynamic memory
 2	sets machine screws and nuts

^{*}Trade mark of National Semiconductor

ASSEMBLY INSTRUCTIONS

DO NOT INSTALL OR SOLDER ANY PARTS UNTIL YOU HAVE READ THE INSTRUCTIONS SEVERAL TIMES AND HAVE FULLY DIGESTED THE INFORMATION!

CAUTION - DO NOT SOLDER OR CLIP COMPONENT LEADS WITHOUT USING SAFETY GLASSES!

INSPECTION

Use the Parts List to make sure that there are no missing items in your kit. Please notify us of any shortages. Be sure that you check for missing parts before you start to assemble the kit.

COMPONENT LEAD WIDTHS

Bend the leads on the resistors, axial capacitors and diodes to their proper widths <u>before</u> insertion so that they will insert easily, solder cleanly, and give the assembled board a professional appearance. If you do not have a bending block, you can make one easily by driving small finishing nails into a block of wood at intervals 4/10 inches apart for 1/2 inch, 4.5/10 inches for .55 inch and 1/2 inch for 6/10 inches. The component leads can be bent over the nails.

All resistors in this kit should have a lead width of 1/2 inch. This is also true for the diodes.

There are a total of twelve 2.7 μ fd tantalum capacitors located within the memory array. These have a lead length of 1/2 inch. There are eight 2.7 μ fd tantalum capacitors located at the <u>top</u> of the memory array -- four of these have lead lengths of 1/2 inch while the other four have lead lengths of 6/10 inches. The four 39 μ fd tantalum capacitors at the <u>top</u> of the memory array have lead lengths of 6/10 inches. There are eight 39 μ fd tantalum capacitors at the <u>bottom</u> of the memory array. The four vertical pieces have 5.5/10 inch lead lengths while the four horizontal have 6/10 inches.

The two 39 μ fd tantalum capacitors near the 7805 +5 volt regulator have lead lengths of 6/10 inches as do the four 2.7 μ fd tantalum capacitors on the side and below the 78M12 +12 volt regulator.

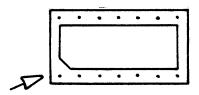
The transistors and disk capacitors have partially formed leads and may be inserted without preparation.

SOCKETS

A socket is furnished for <u>every</u> integrated circuit. It is important that you use these sockets, otherwise a defective part will be extremely difficult to replace. <u>NO REPAIR OR SERVICE WILL BE PERFORMED ON A KIT WHICH HAS HAD INTEGRATED CIRCUITS SOLDERED TO THE CIRCUIT BOARD</u>.

PARTS ORIENTATION

In all references throughout the instructions, the convention used is that the gold edge connector is the bottom of the board. Orientation identification is molded into the plastic of the sockets and is illustrated below.



This orientation marks identifies where pin #1 of the integrated circuit is to be positioned when it is plugged into the socket. The sockets should be inserted in the board so that the orientation mark is in the lower left hand corner.

Orientation of the transistors, tantalum capacitors, diodes and voltage regulators is specified in the component layout drawing. Be sure to study this drawing and the 8x10 glossy photograph <u>carefully</u> before building the kit. Refer to both during parts installation.

The DIP switch occupies position 1F on the circuit board and should be oriented so that switch #1 is on the left. The "off" position for all switches is then in the down direction while the "on" position is toward the top.

SOLDERING AND SOLDER IRONS

A minature style 18 watt iron with a fine tip is ideal for constructing this kit. Do not use an iron of more than 25 watts under any circumstance. In any event, the tip should be small. If too much heat is applied to the board, the copper traces will lift. The most desirable soldering iron for complex electronic kits is a constant temperature tool. These are somewhat more expensive but will make a good investment for the serious kit builder.

As a general rule, bend the component leads and socket pins only enough to hold the part to the board until it is soldered. Even though a protective solder mask has been applied to the circuit board, excessive solder can still cause bridges where leads are close together. It is important to economize on solder. Use only enough to cover the joint and leave the iron on the pad just long enough to cause the solder to flow throughout the joint.

The ground and power pads of the voltage regulators and tantalum capacitors adjacent to the regulators are designed so that these components will solder to their pads without absorbing too much heat from the iron. The 18 watt iron will supply enough heat without burning up components or lifting solder pads.

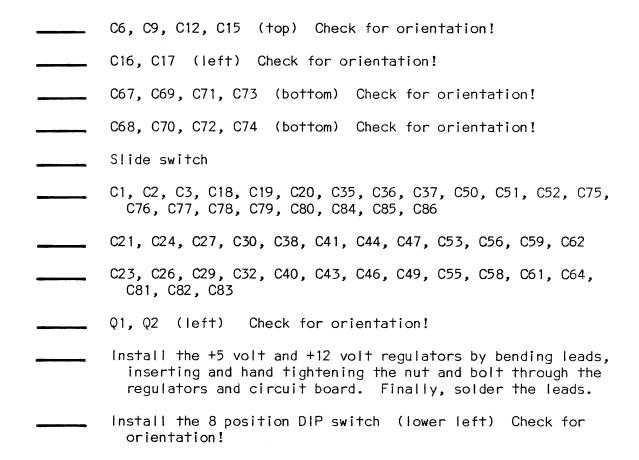
DO NOT INSTALL OR SOLDER ANY PARTS UNTIL YOU HAVE READ THESE INSTRUCTIONS CAREFULLY!

CAUTION - DO NOT SOLDER CLIP COMPONENT LEADS WITHOUT USING SAFETY GLASSES!

PARTS INSTALLATION

Before installing parts, bend the leads of the resistors, diodes and tantalum capacitors to their proper lengths. After a series of parts have been installed in the board, bend the leads slightly to hold them in place. Solder the leads and trim the excess lead length before proceeding to the next series.

Install C4, C7, C10, C13 (top of board) Check for orientation! C5, C8, C11, C14 (top of board) Check for orientation! C22, C25, C28, C31 (upper) Check for orientation! C33, C34 (middle left) Check for orientation! C39, C42, C45, C48 (middle) Check for orientation! C54, C57, C60, C63 (middle) Check for orientation! C65. C66 (left) Check for orientation! R1 (top) R2, R3 (middle) R4, R5, R6, R7 (left) R8, R9, R10 (left) R11 - R18 (lower left) CR1 (left) Check for orientation! CR2 - CR5 (lower left) Check for orientation! Sockets 3A, 1B, 2B, 3B, 1C, 2C, 3C, 1D, 2D, 3D, 1E, 2E, 3E, 2F, 3F Check for orientation! Sockets 4A, 5A, 6A, 7A, 4B, 5B, 6B, 7B, 4C, 5C, 6C, 7C, 4D, 5D, 6D, 7D Check for orientation! Sockets 4E, 5E, 6E, 7E Check for orientation!



POWER-UP AND SYSTEM CHECK OUT

POWER SUPPLY/VOLTAGE REGULATOR CHECK OUT

Voltage requirements: (reference to ground connector pins 50 and 100)

Pins 1 and 51 not less than 7 volts approx. 260 ma

not more than 10 volts

Pin 2 not less than 14 volts

not more than 22 volts approx. 80 ma

Pin 52 not less than -22 volts

not more than -7 volts approx. 20 ma

Before installing any of the integrated circuits, apply power to pins 1 and 51, pin 2, and pin 52 (ground pins 50 and 100) of the edge connector as specified above. Perform the following measurements with a volt meter.

(1) Pin 18 of 4D +12 volts

(2) Pin 18 of 7D +12 volts

(3) Pin 1 of 4A -5 volts

(4) Pin 1 of 7A -5 volts

(5) Pin 11 of 4D +5 volts

(6) Pin 11 of 7D +5 volts

(7) Pin 20 of 7E +5 volts

(8) Pin 16 of 4D +5 volts

(9) Pin 24 of 3F +5 volts

(10) Pin 14 of 1E +5 volts

If the voltage at any of the check points differs from the required value, return the board for trouble shooting and repair.

POWER-UP CHECK OUT

Install the integrated circuits as per the layout sheet. When inserting these parts, be careful about bending pins under the package — a pin which is bent under the integrated circuit may appear to be inserted in the socket. Many of the units will be shipped with memorys which are housed in ceramic packages with pins brazed to the side of the device. These pins are slightly wider than the pins of plastic parts and as a result are somewhat harder to

insert into new IC sockets. The best way to handle this problem is to tilt the part slightly so that one end goes into the socket slightly before the other.

After all parts have been installed, voltages checked and integrated circuits installed, configure the address selection switches to a convenient address block, insert the board and power up your computer. Through either the front panel or system monitor, do several examines and deposits in block A and block B. Be sure the write protect switch is in the write enabled position. If any problem occurs when data is written into either block, return the board for trouble shooting and repair.

Next, read the memory test section of this manual carefully. Load and initialize the memory test program and then start it. If errors occur, return the board. Most of the problems with malfunctioning boards are either errors in construction or faulty parts. However, the operation of dynamic memory units is somewhat more complex than static boards and therefore more difficult to trouble shoot. So, if the board has been properly assembled but does not work, it will save time and be less frustrating if the memory is returned for check out, repair and testing.

WARRANTY

Parts are warranted to be free from defects in material and work-manship. Defective parts returned postpaid will be exchanged free of charge. ThinkerToy products purchased in kit form are warranted for six months from date of invoice. ThinkerToy products purchased as assembled units are warranted for one year from invoice date. Malfunctioning units whether purchased in kit form or pre-assembled will be repaired, tested, and returned with a minimal charge for postage/handling if in the opinion of Morrow's Micro-Stuff or ThinkerToys care has been exercised in their assembly and/or use. If on inspection by Morrow's, it is found that the product has been subject to improper assembly or abuse, charges will be assessed accordingly for repair parts and labor. Repair fees will not exceed \$25.00 unless prior approval has been obtained from purchaser.

The foregoing warranty is in lieu of all other warranties expressed or implied and in any event is limited to product repair or replacement.

COMPATIBILITY

The Synchrofresh memory design is very simple. It requires no delay lines, one shots, or on-board crystal oscillators. This simplicity results in lower cost and higher reliability; however, this simplicity has a trade off. Synchrofresh design requires that the timing relationships on the S-100 buss be well defined so that invisible refresh can be woven into normal memory cycles. Specifically, the timing relations between ϕ_2 , PSYNC, PDBIN and \overline{PWR} must closely resemble the natural sequencing of the 8080A. Unfortunately, there are a number of processor boards and DMA units which plug into the S-100 buss whose timing is considerably different from the classic 8080A signals. The devices which are known not to work with the Synchrofresh 8K memory are:

- 1. TDL Z-80 CPU board
- 2. SD Sales Z-80 CPU board
- 3. Mini-term DMA video board
- 4. Digital Systems DMA disk controller
- 5. Cromenco Dazzler DMA video board.

Care should be exercised whenever the memory is used with a DMA device or a Z80 CPU board. If the timing signals of these devices are reasonably close to those of the classic 8080A signals, the memory should perform flawlessly. If the differences are too great, the memory may fail. In such an event, we ask that the customer return the memory so that the purchase price can be refunded.